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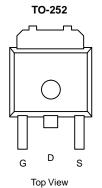
# N-Channel 150 V (D-S) MOSFET

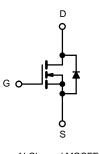
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$ Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)	
150	$0.065 \text{ at V}_{GS} = 10 \text{ V}$	30	39.8	
	0.070 at V <sub>GS</sub> = 4.5 V	15.2	39.0	

#### **FEATURES**

- DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:







N-Channel MOSFET

## **APPLICATIONS**

- DC/DC Converters
- DC/AC Inverters
- Motor Drives

ABSOLUTE MAXIMUM RA	<b>TINGS</b> ( $T_C = 25  ^{\circ}C$ , unless of	otherwise noted)		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	150	V
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current	T <sub>C</sub> = 25 °C		30	
Continuous Diain Current	T <sub>C</sub> = 70 °C	I <sub>D</sub>	15.2	A
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	90	
Avalanche Current		I <sub>AS</sub>	15	
Single Avalanche Energy <sup>a</sup> L = 0.1 mH		E <sub>AS</sub>	81.25	mJ
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	D	91.7 <sup>b</sup>	W
	T <sub>A</sub> = 25 °C <sup>c</sup>	P <sub>D</sub>	1.1	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	60	°C/W
Junction-to-Case (Drain)	R <sub>thJC</sub>	1	C/VV

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Base on  $T_C$  = 25 °C.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	150			
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5		4	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V			1	μA
	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
D : 0	_	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.6 A		0.065	0.076	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 6 \text{ A}$		0.070	0.080	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6.6 A		25		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			1810		pF
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		65		
Reverse Transfer Capacitance	C <sub>rss</sub>			45		
Total Gate Charge <sup>c</sup>	Qg			39.8	50	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 6.6 \text{ A}$		9.6		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			14.1		
Gate Resistance	R <sub>q</sub>	f = 1 MHz	0.4	2	4	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	16	
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V, R}_{1} = 9.6 \Omega$		11	20	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 5.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		18	27	
Fall Time <sup>c</sup>	t <sub>f</sub>			5	10	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			38	57	ns
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V, } R_1 = 9.6 \Omega$		58	87	- - -
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 5.2 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		18	27	
Fall Time <sup>c</sup>	t <sub>f</sub>	, i		8	16	
Drain-Source Body Diode Ratings a	nd Characteri	stics <sup>b</sup> T <sub>C</sub> = 25 °C		L		
Continuous Current	Is				30	
Pulsed Current	I <sub>SM</sub>				90	A
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 5.2 A, V <sub>GS</sub> = 0 V		0.8	1.5	V
Reverse Recovery Time	t <sub>rr</sub>			34	51	ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 5.2 A, dI/dt = 100 A/μs		3	5	Α
Reverse Recovery Charge	Q <sub>rr</sub>	<u> </u>		50	75	nC

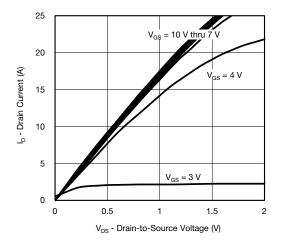
## Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

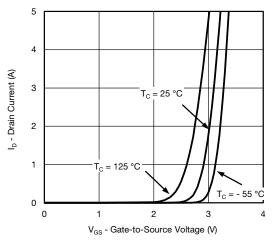
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



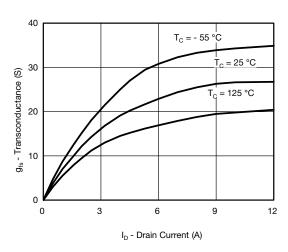
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



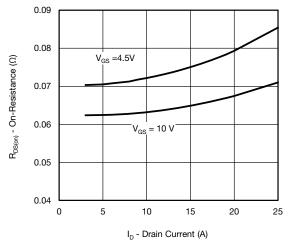
#### **Output Characteristics**



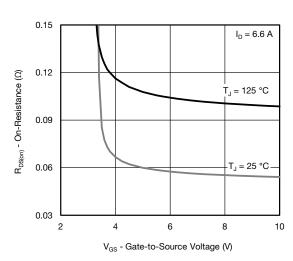
**Transfer Characteristics** 



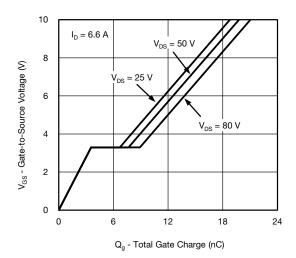
Transconductance



On-Resistance vs. Drain Current



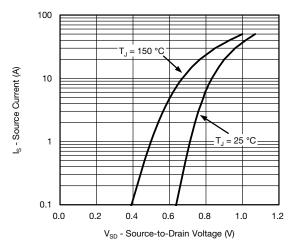
On-Resistance vs. Gate-to-Source Voltage



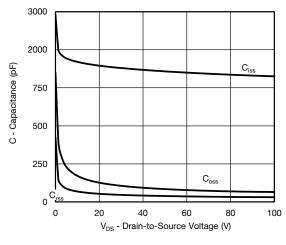
**Gate Charge** 



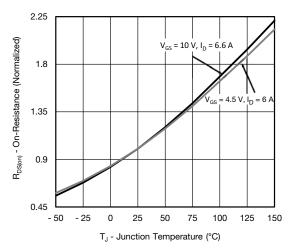
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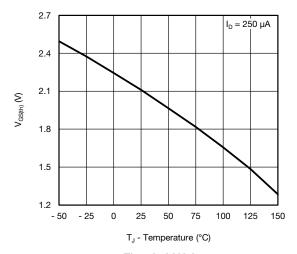
#### Source-Drain Diode Forward Voltage



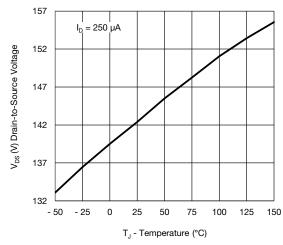
#### Capacitance



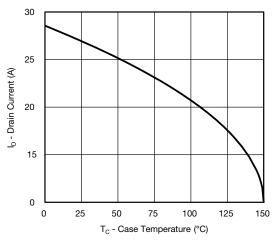
On-Resistance vs. Junction Temperature



#### Threshold Voltage



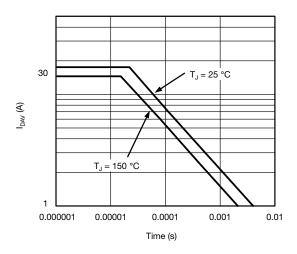
Drain Source Breakdown vs. Junction Temperature

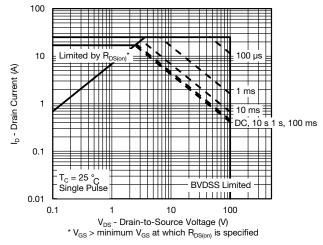


**Current Derating** 



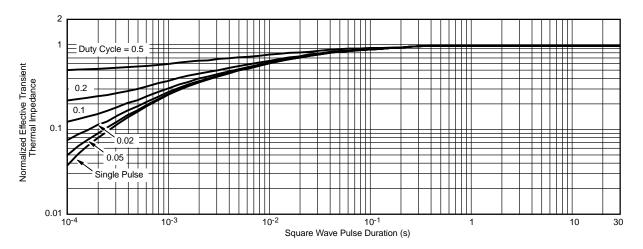
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Avalanche Current Capability vs. Time





Normalized Thermal Transient Impedance, Junction-to-Case

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